FAIRCHILD

SEMICONDUCTOR

74LVT32244 • 74LVTH32244 Low Voltage 32-Bit Buffer/Line Driver with 3-STATE Outputs (Preliminary)

General Description

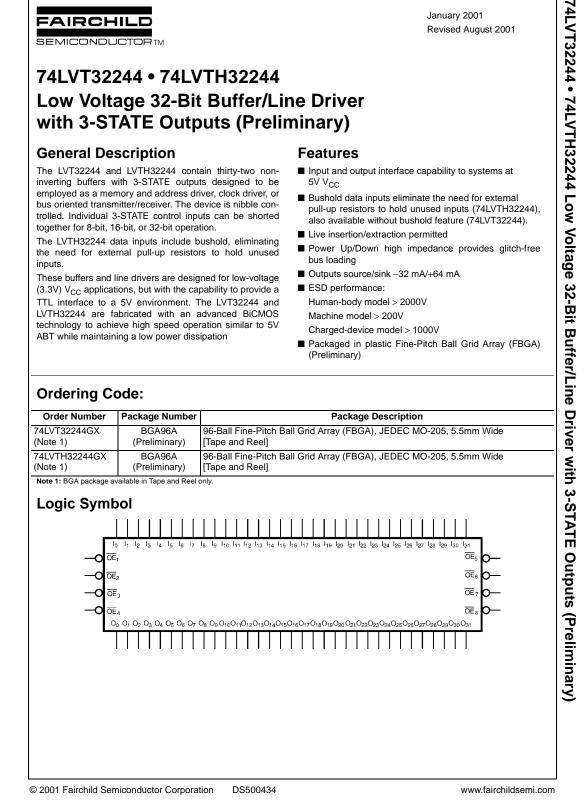
The LVT32244 and LVTH32244 contain thirty-two noninverting buffers with 3-STATE outputs designed to be employed as a memory and address driver, clock driver, or bus oriented transmitter/receiver. The device is nibble controlled. Individual 3-STATE control inputs can be shorted together for 8-bit, 16-bit, or 32-bit operation.

The LVTH32244 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These buffers and line drivers are designed for low-voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVT32244 and LVTH32244 are fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining a low power dissipation

Features

- Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH32244),
- also available without bushold feature (74LVT32244).
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink –32 mA/+64 mA
- ESD performance:
- Human-body model > 2000V Machine model > 200V
- Charged-device model > 1000V ■ Packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)



January 2001 Revised August 2001

Connection	Diagram
	123456
A	000000
ш	000000
O	000000
۵	000000
ш	000000
ш	000000
ហ	000000
т	000000
ر	000000
¥	000000
	000000
Σ	000000
z	000000
<u>م</u>	000000
ш	000000
F	000000
	(Top Thru View)

Pin Descriptions

Pin Names	Description
OE _n	Output Enable Input (Active LOW)
I ₀ —I ₃₁	Inputs
O ₀ –O ₃₁	Outputs

Pin Assignments for FBGA

	1	2	3	4	5	6
Α	01	O ₀	OE ₁	\overline{OE}_2	I ₀	I ₁
В	O ₃	0 ₂	GND	GND	l ₂	I ₃
С	0 ₅	O ₄	V _{CC1}	V _{CC1}	I ₄	I_5
D	0 ₇	0 ₆	GND	GND	I ₆	۱ ₇
E	0 ₉	O ₈	GND	GND	I ₈	l ₉
F	0 ₁₁	O ₁₀	V _{CC1}	V _{CC1}	I ₁₀	I ₁₁
G	0 ₁₃	0 ₁₂	GND	GND	I ₁₂	I ₁₃
н	O ₁₄	0 ₁₅	\overline{OE}_4	\overline{OE}_3	I ₁₅	I ₁₄
J	O ₁₇	O ₁₆	\overline{OE}_5	\overline{OE}_6	I ₁₆	I ₁₇
к	0 ₁₉	0 ₁₈	GND	GND	I ₁₈	I ₁₉
L	0 ₂₁	O ₂₀	V _{CC2}	V _{CC2}	I ₂₀	I ₂₁
м	O ₂₃	O ₂₂	GND	GND	I ₂₂	I ₂₃
N	O ₂₅	O ₂₄	GND	GND	I ₂₄	I ₂₅
Р	0 ₂₇	0 ₂₆	V _{CC2}	V _{CC2}	I ₂₆	I ₂₇
R	O ₂₉	O ₂₈	GND	GND	I ₂₈	I ₂₉
т	O ₃₀	O ₃₁	OE ₈	OE ₇	I ₃₁	I ₃₀

In	puts	Outputs
OE ₁	I ₀ -I ₃	O ₀ -O ₃
L	L	L
L	н	н
Н	Х	Z
	puts	Outputs
DE ₂	I ₄ -I ₇	0 ₄ -0 ₇
L	L	L
L	Н	H
H	Х	Z
In	puts	Outputs
)E ₃	I ₈ -I ₁₁	0 ₈ –0 ₁₁
L	L	L
L	Н	Н
H	Х	Z
In	puts	Outputs
E ₄	I ₁₂ -I ₁₅	0 ₁₂ -0 ₁₅
L	L	L
L	Н	Н
Н	Х	Z
In	puts	Outputs
)E ₅	I ₁₆ -I ₁₉	0 ₁₆ -0 ₁₉
L	L	L
L	Н	H
H	Х	Z
	puts	Outputs
DE ₆	I ₂₀ -I ₂₃	O ₂₀ -O ₂₃
L L	L	L
L	H X	H Z
		۷ ک
Н		
H In	puts	Outputs
H In DE ₇	puts	0 ₂₄ -0 ₂₇
H Inj DE ₇	puts	0 ₂₄ -0 ₂₇ L
H Inj DE ₇ L L	L H	О₂₄-О₂₇ L H
H Inj DE ₇ L H	риts I ₂₄ -I ₂₇ L Н Х	0 ₂₄ -0 ₂₇ L H Z
H DE ₇ L L H	puts	O ₂₄ -O ₂₇ L H Z Outputs
H DE ₇ L L H In DE ₈	I24-I27 L H X puts I28-I31	024-027 L H Z Outputs 028-031
H Inj DE7 L L H	puts	O ₂₄ -O ₂₇ L H Z Outputs O ₂₈ -O ₃₁ L
 - - - 	I24-I27 L H X puts I28-I31	024-027 L H Z Outputs 028-031

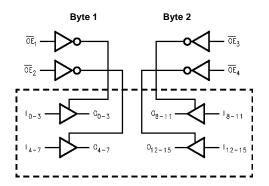
H = HGH Voltage Level L = LOW Voltage Level X = Immaterial (HIGH or LOW, inputs may not float) Z = High Impedance

Functional Description

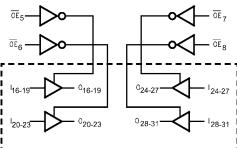
The 74LVT32244 and 74LVTH32244 contain thirty-two non-inverting buffers with 3-STATE outputs. The device is nibble (4 bits) controlled with each nibble functioning identically, but independent of the other. The control pins can be shorted together to obtain full 32-bit operation. The

Logic Diagrams

3-STATE outputs are controlled by an Output Enable (\overline{OE}_n) input. When \overline{OE}_n is LOW, the outputs are in the 2-state mode. When \overline{OE}_n is HIGH, the standard outputs are in the high impedance mode but this does not interfere with entering new data into the inputs.



Byte 3 Byte 4



 $V_{\mbox{\scriptsize CC1}}$ is associated with Bytes 1 and 2.

 V_{CC2} is associated with Bytes 3 and 4.

Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Symbol	Parameter	Value	Conditions	Units	
V _{CC}	Supply Voltage	-0.5 to +4.6		V	
VI	DC Input Voltage	-0.5 to +7.0		V	
Vo	Output Voltage	-0.5 to +7.0	Output in 3-STATE	V	
		-0.5 to +7.0	Output in High or Low State (Note 3)	v	
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA	
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA	
l _o	DC Output Current	64	V _O > V _{CC} Output at HIGH State	mA	
		128	V _O > V _{CC} Output at LOW State	- 111A	
I _{CC}	DC Supply Current per Supply Pin	±64		mA	
GND	DC Ground Current per Ground Pin	±128		mA	
T _{STG}	Storage Temperature	-65 to +150		°C	

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{cc}	Supply Voltage	2.7	3.6	V
/1	Input Voltage	0	5.5	V
ОН	High-Level Output Current		-32	mA
OL	Low-Level Output Current		64	mA
Γ _A	Free Air Operating Temperature	-40	+85	°C
Δt/ΔV	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 2: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied. Note 3: I_O Absolute Maximum Rating must be observed.

DC Electrical Characteristics

Symbol	Deven	Parameter		$T_A = -40^{\circ}C$	to +85°C	Units	Conditions	
Symbol	Falameter		(V)	Min	Max	Units	Conditions	
V _{IK}	Input Clamp Diode Vo	oltage	2.7		-1.2	V	I _I = -18 mA	
VIH	Input HIGH Voltage		2.7–3.6	2.0		V	$V_0 \le 0.1V$ or	
VIL	Input LOW Voltage		2.7–3.6		0.8	V	$V_{O} \ge V_{CC} - 0.1V$	
V _{OH}	Output HIGH Voltage		2.7–3.6	V _{CC} - 0.2			I _{OH} = -100 μA	
			2.7	2.4		V	I _{OH} = -8 mA	
			3.0	2.0			$I_{OH} = -32 \text{ mA}$	
V _{OL}	Output LOW Voltage		2.7		0.2		I _{OL} = 100 μA	
			2.7		0.5		I _{OL} = 24 mA	
			3.0		0.4	V	I _{OL} = 16 mA	
			3.0		0.5		I _{OL} = 32 mA	
			3.0		0.55		I _{OL} = 64 mA	
I _{I(HOLD)}	Bushold Input Minimum Drive		3.0	75		μA	$V_{l} = 0.8V$	
(Note 4)				-75		μΑ	$V_{I} = 2.0V$	
I _{I(OD)}	Bushold Input Over-Drive Current to Change State		3.0	500		μA	(Note 5)	
(Note 4)				-500		μΑ	(Note 6)	
l _l	Input Current		3.6		10		$V_{I} = 5.5V$	
		Control Pins	3.6		±1	μA	$V_I = 0V \text{ or } V_{CC}$	
		Data Pins	3.6		-5	μΑ	$V_I = 0V$	
		Data Tino	0.0		1		$V_I = V_{CC}$	
I _{OFF}	Power Off Leakage Current		0		±100	μΑ	$0V \le V_I \text{ or } V_O \le 5.5V$	
I _{PU/PD}	Power Up/Down		0 – 1.5V		±100	μA	$V_{O} = 0.5V$ to 3.0V	
	3-STATE Current		0 - 1.50		100	μΑ	$V_I = GND \text{ or } V_{CC}$	
l _{OZL}	3-STATE Output Leak	age Current	3.6		-5	μΑ	$V_0 = 0.5V$	
I _{OZH}	3-STATE Output Leak	age Current	3.6		5	μΑ	V _O = 3.0V	
I _{OZH} +	3-STATE Output Leak	age Current	3.6		10	μΑ	$V_{CC} < V_O \le 5.5V$	

DC Electrical Characteristics (Continued)

Symbol	Parameter		v _{cc}	T _A = -40°C to +85°C Min Max		Units	Conditions
Symbol	Farameter		(V)			Units	Conditions
I _{CCH}	Power Supply Current V _C	C1 or V _{CC2}	3.6		0.19	mA	Outputs High
I _{CCL}	Power Supply Current V _C	C1 or V _{CC2}	3.6		5.0	mA	Outputs Low
I _{CCZ}	Power Supply Current V _C	C1 or V _{CC2}	3.6		0.19	mA	Outputs Disabled
I _{CCZ} +	Power Supply Current V _C	C1 or V _{CC2}	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$,
							Outputs Disabled
ΔI_{CC}	Increase in Power Supply Curre	ent	3.6		0.2	mA	One Input at V _{CC} – 0.6V
	(Note 7) V _C	C1 or V _{CC2}					Other Inputs at V _{CC} or GND

Note 4: Applies to bushold versions only (LVTH32244).

Note 5: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 6: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 7: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 8)

Symbol	Parameter	V _{cc}	$T_A = 25^{\circ}C$			$T_A = 25^{\circ}C$		_A = 25°C Uni		Conditions
Cymbol	i arameter	(V)	Min	Typ Max		onna	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$			
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 9)			
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 9)			

Note 8: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 9: Max number of outputs defined as (n). n–1 data inputs are driven 0V to 3V. Output under test held LOW.

AC Electrical Characteristics

Symbol	Parameter		$T_A = -40^{\circ}C$ to $+85^{\circ}C$ $C_L = 50$ pF, $R_L = 500\Omega$					
	Parameter	V _{CC} = 3.	$V_{CC}=3.3V\pm0.3V$		$V_{CC} = 2.7V$			
		Min	Min Max Min Ma	Max	t			
t _{PLH}	Propagation Delay Data to Output	1.2	3.5	1.2	3.9			
t _{PHL}		1.2	3.5	1.2	3.9	ns		
t _{PZH}	Output Enable Time	1.2	4.0	1.2	5.0	ns		
t _{PZL}		1.2	5.0	1.2	6.5	115		
t _{PHZ}	Output Disable Time	2.0	4.7	2.0	5.2			
t _{PLZ}		1.5	4.2	1.5	4.4	ns		

Capacitance (Note 10)

Symbol	Parameter	Conditions	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 0V$, $V_I = 0V$ or V_{CC}	4	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.0$ V, $V_{O} = 0$ V or V_{CC}	8	pF
Note 10: Consoitor	ce is measured at frequency f - 1 MHz ne	r MIL STD 992 Mothod 2012		

lote 10: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012

